

# Patrick Stephen Goley

## List of Publications by Year in descending order

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Version: 2024-02-01

20  
papers

361  
citations

933447

10  
h-index

839539

18  
g-index

20  
all docs

20  
docs citations

20  
times ranked

548  
citing authors

#	ARTICLE	IF	CITATIONS
1	Germanium Based Field-Effect Transistors: Challenges and Opportunities. <i>Materials</i> , 2014, 7, 2301-2339.	2.9	129
2	Strain-Engineered Biaxial Tensile Epitaxial Germanium for High-Performance Ge/InGaAs Tunnel Field-Effect Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2015, 3, 184-193.	2.1	33
3	Heterogeneous Integration of Epitaxial Ge on Si using AlAs/GaAs Buffer Architecture: Suitability for Low-power Fin Field-Effect Transistors. <i>Scientific Reports</i> , 2014, 4, 6964.	3.3	26
4	Heterogeneously-Grown Tunable Tensile Strained Germanium on Silicon for Photonic Devices. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 26470-26481.	8.0	23
5	Integration of SrTiO <sub>3</sub> on Crystallographically Oriented Epitaxial Germanium for Low-Power Device Applications. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 5471-5479.	8.0	22
6	Heterointerface Engineering of Broken-Gap InAs/GaSb Multilayer Structures. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 2512-2517.	8.0	21
7	Potential Limitations on Integrated Silicon Photonic Waveguides Operating in a Heavy Ion Environment. <i>IEEE Transactions on Nuclear Science</i> , 2018, 65, 141-148.	2.0	18
8	Heteroepitaxial Ge MOS Devices on Si Using Composite AlAs/GaAs Buffer. <i>IEEE Journal of the Electron Devices Society</i> , 2015, 3, 341-348.	2.1	16
9	Optical Single-Event Transients Induced in Integrated Silicon-Photonic Waveguides by Two-Photon Absorption. <i>IEEE Transactions on Nuclear Science</i> , 2021, 68, 785-792.	2.0	14
10	Design, Theoretical, and Experimental Investigation of Tensile-Strained Germanium Quantum-Well Laser Structure. <i>ACS Applied Electronic Materials</i> , 2021, 3, 4535-4547.	4.3	13
11	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. <i>IEEE Transactions on Nuclear Science</i> , 2019, 66, 125-133.	2.0	11
12	Magnetotransport Properties of Epitaxial Ge/AlAs Heterostructures Integrated on GaAs and Silicon. <i>ACS Applied Materials &amp; Interfaces</i> , 2015, 7, 22315-22321.	8.0	9
13	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 71-80.	2.0	7
14	Response of Waveguide-Integrated Germanium-on-Silicon p-i-n Photodiodes to Neutron Displacement Damage. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 296-304.	2.0	6
15	Mixed-anion GaAs <sub>1-x</sub> Ge <sub>x</sub> /Sb <sub>y</sub> graded buffer heterogeneously integrated on Si by molecular beam epitaxy. <i>Applied Physics Express</i> , 2015, 8, 025501.	2.4	4
16	Single-Event Transients in SiGe HBTs Induced by Pulsed X-Ray Microbeam. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 91-98.	2.0	4
17	Electronic-to-Photonic Single-Event Transient Propagation in a Segmented Mach-Zehnder Modulator in a Si/SiGe Integrated Photonics Platform. <i>IEEE Transactions on Nuclear Science</i> , 2020, 67, 260-267.	2.0	3
18	Localized Excitation of Silicon Photonic Waveguides for Measurement of Free-Carrier Lifetime and Surface Recombination Velocity. , 2021, , .		1

#	ARTICLE	IF	CITATIONS
19	Modeling Transient Loss Due to Ionizing Particles in Silicon Photonic Waveguides. IEEE Transactions on Nuclear Science, 2022, 69, 518-526.	2.0	1
20	Zero-Process-Change SiGe Heterojunction Avalanche Photodiode for High-Speed, High-Gain Detection Near the Silicon Band Edge. IEEE Electron Device Letters, 2021, 42, 1260-1263.	3.9	0